

Serial No. 09/843,783
Art Unit: 2823

Rejection Under 35 USC 102/103

To the extent any art rejection continues to be applied against claims 1 and 15, reconsideration is respectfully requested.

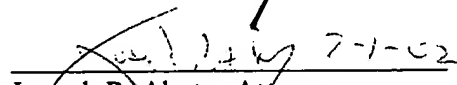
Neither Czubytyj ('690) nor Furukawa ('614), whether applied singly or in combination, teaches, discloses or suggests Applicant's method which includes "supplying a dopant precursor to the substrate according to a relationship of the precursors as shown in Fig. 2" of the Application as filed.

Accordingly, entry of this Amendment, reconsideration of claims 1-9, 15 are solicited.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. **This appendix is captioned "Version with Markings to Show Changes Made".**

Respectfully submitted,
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By:


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Attachment: Appendix - Version with Markings to Show Changes Made

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

Kindly amend independent claims 1 and 15 as follows:

1. (Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, wherein said step of doping while supplying includes supplying a dopant precursor to the substrate according to a relationship of the precursors as shown in Fig. 2.

15. (Amended) A method of growing a film without sharp pressure transitions, comprising:

carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, wherein said step of doping while supplying includes supplying a dopant precursor to the substrate according to a relationship of the precursors as shown in Fig. 2.